

# **OPAx237 Single-Supply Operational Amplifiers MicroAmplifier Series**

#### 1 Features

Micro-size, miniature packages:

 Single: SOT23-5, SO-8 Dual: VSSOP-8, SO-8 Quad: SSOP-16 (obsolete)

Low offset voltage: 750µV max (V<sub>S</sub>=5V)

Wide supply range:

 Single supply: 2.7V to 36V Dual supply: ±1.35V to ±18V Low quiescent current: 350µA max

Wide bandwidth: 1.5MHz

## 2 Applications

Battery-powered instruments

Portable devices

PCMCIA cards

Medical instruments

Test equipment

## 3 Description

The OPAx237 op amp family is one of Texas Instruments' MicroAmplifier series of miniature products. In addition to small size, these devices feature low offset voltage, low quiescent current, low bias current, and a wide supply range. Single, and dual versions have identical specifications for maximum design flexibility. These devices are designed for single-supply, battery-operated, and space-limited applications, such as PCMCIA cards and other portable instruments.

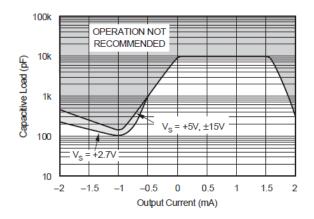
The OPAx237 series op amps operate from either single or dual supplies. When operated from a single supply, the input common-mode range extends below ground and the output can swing to within 10mV of ground. Dual and quad designs feature completely independent circuitry for lowest crosstalk and freedom from interaction.

Single, dual, and quad versions are offered in spacesaving surface-mount packages. The single version is available in the ultra-miniature 5-lead SOT23-5 and SOIC-8 surface-mount packages. The dual version comes in miniature VSSOP-8 and SO-8 surfacemount packages. The quad version is obsolete. The VSSOP-8 has the same lead count as a the SO-8, but at half the size. The SOT23-5 is even smaller, at one-fourth the size of an SOIC-8. All are specified for -40°C to +85°C operation. A macromodel is available for design analysis.

#### **Device Information**

PRODUCT	CHANNELS	PACKAGE <sup>(1)</sup>
OPA237		D (SOIC, 8)
UPA237	Single	DBV (SOT-23, 5)
OPA2237	Dual	D (SOIC, 8)
OFA2231	Duai	DGK (VSSOP, 8)

For more information, see Section 9.



**Stability-Capacitive Load vs Output Current** 



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# **4 Pin Configuration and Functions**

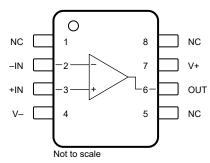


Figure 4-1. OPA237: D Package, 8-Pin SOIC (Top View)

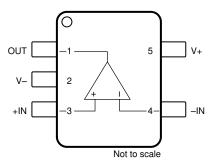


Figure 4-2. OPA237: DBV Package, 5-Pin SOT-23 (Top View)

Table 4-1. Pin Functions: OPA237

	PIN			
NAME	NO.		TYPE	DESCRIPTION
NAME	D (SOIC)	DBV (SOT-23)		
-IN	2	4	Input	Inverting input
+IN	3	3	Input	Noninverting input
OUT	6	1	Output	Output
V-	4	2	Power	Negative (lowest) power supply
V+	7	5	Power	Positive (highest) power supply

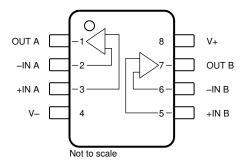


Figure 4-3. OPA2237: D Package, 8-Pin SOIC, and DGK Package, 8-Pin VSSOP (Top View)

Table 4-2. Pin Functions: OPA2237

PIN		TYPE	DESCRIPTION	
NAME	NO.	ITPE	DESCRIPTION	
–IN A	2	Input	Inverting input, channel A	
+IN A	3	Input	Noninverting input, channel A	
–IN B	6	Input	Inverting input, channel B	
+IN B	5	Input	Noninverting input, channel B	
OUT A	1	Output	Output, channel A	
OUT B	7	Output	Output, channel B	
V-	4	Power	Negative (lowest) power supply	
V+	8	Power	Positive (highest) power supply	



## **5 Specifications**

## 5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

				MIN	MAX	UNIT
Vs	Supply voltage, V <sub>S</sub> = (	V+) – (V–)			36	V
		Voltage	Common-mode	(V-) - 0.7	(V+) + 0.7	V
	Signal input pins	Signal input pins Voltage	Differential	-0.7	+0.7	v
		Current			±10	mA
I <sub>SC</sub>	Output short circuit(2)			Continuous		
T <sub>A</sub>	Operating temperature	)		<b>–</b> 55	125	°C
TJ	Junction temperature				150	°C
T <sub>stg</sub>	Storage temperature			<b>–</b> 55	125	°C

<sup>(1)</sup> Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute Maximum Ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If used outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.

## **5.2 Recommended Operating Conditions**

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM MAX	UNIT
Vs	Supply voltage, $V_S = (V+) - (V-)$	2.7	36	V
T <sub>A</sub>	Operating temperature	-40	85	°C

#### 5.3 Thermal Information OPA237

		OPA	OPA237			
	THERMAL METRIC <sup>(1)</sup>	DBV (SOT-23)	D (SOIC)	UNIT		
		5 PINS	8 PINS			
$R_{\theta JA}$	Junction-to-ambient thermal resistance	115.8	180.4	°C/W		
R <sub>θJC(top)</sub>	Junction-to-case (top) thermal resistance	56.4	67.9	°C/W		
$R_{\theta JB}$	Junction-to-board thermal resistance	56.4	102.1	°C/W		
ΨЈТ	Junction-to-top characterization parameter	12.8	10.4	°C/W		
ΨЈВ	Junction-to-board characterization parameter	55.9	100.3	°C/W		
R <sub>0JC(bot)</sub>	Junction-to-case (bottom) thermal resistance	N/A	N/A	°C/W		

<sup>(1)</sup> For information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application note.

#### 5.4 Thermal Information OPA2237

		OF	OPA2237			
	THERMAL METRIC(1)	D (SOIC)	DGK (VSSOP)	UNIT		
		8 PINS	8 PINS			
$R_{\theta JA}$	Junction-to-ambient thermal resistance	126.9	175.6	°C/W		
R <sub>0JC(top)</sub>	Junction-to-case (top) thermal resistance	67.1	63.1	°C/W		
$R_{\theta JB}$	Junction-to-board thermal resistance	70.3	97.2	°C/W		
ΨЈΤ	Junction-to-top characterization parameter	18.8	7.8	°C/W		
ΨЈВ	Junction-to-board characterization parameter	69.5	95.5	°C/W		
R <sub>0JC(bot)</sub>	Junction-to-case (bottom) thermal resistance	N/A	N/A	°C/W		

(1) For information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application note.

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<sup>(2)</sup> Short-circuit to ground, one amplifier per package.

# 5.5 Electrical Characteristics for $V_S = 2.7V$

at  $T_A$  = 25°C,  $V_O$  =  $V_S$  / 2, and  $R_L$  = 10k $\Omega$  connected to  $V_S$  / 2 (unless otherwise noted)

	PARAMETER	TEST COND	ITIONS	MIN	TYP	MAX	UNIT
OFFSET \							
V <sub>OS</sub>	Input offset voltage	V <sub>CM</sub> = 1V			±250	±950	μV
dV <sub>OS</sub> /dT	Input offset voltage drift	T <sub>A</sub> = -40°C to +85°C			±2	±7.5	μV/°C
PSRR	Power-supply rejection ratio	2.7V < V <sub>S</sub> < 36V			10	30	μV/V
	Channel separation (dual)	-			0.5		μV/V
INPUT BIA	AS CURRENT						-
I <sub>B</sub>	Input bias current (1)	V <sub>CM</sub> = 1V			-10	-40	nA
I <sub>os</sub>	Input offset current (1)	V <sub>CM</sub> = 1V			±0.5	±10	nA
NOISE							
	Input voltage noise	f = 0.1Hz to 10Hz			1		$\mu V_{PP}$
e <sub>n</sub>	Input voltage noise density	f = 1kHz			28		nV/√ <del>Hz</del>
i <sub>n</sub>	Input current noise density	f = 1kHz			60		pA/√ <del>Hz</del>
INPUT VO	DLTAGE						
V <sub>CM</sub>	Common-mode voltage			(V-) - 0.2		(V+) - 1.5	V
CMRR	Common-mode rejection ratio	V <sub>CM</sub> = (V–) – 0.2V to (V+) – 1.5V		71	85		dB
INPUT IMI	PEDANCE						
_		Differential	 Differential		5    4		MΩ    pF
Z <sub>IN</sub>	Input impedance	Common-mode			5    2		TΩ    pF
OPEN-LO	OP GAIN						
A <sub>OL</sub>	Open-loop voltage gain	V <sub>O</sub> = 0.55V to 1.7V		75	88		dB
FREQUEN	NCY RESPONSE						
GBW	Gain bandwidth product				1.2		MHz
SR	Slew rate	G = 1			0.45		V/µs
	0-441	0 = 4.0 = 400=5.4\/ =t==	0.1%		5		
t <sub>S</sub>	Settling time	$G = -1$ , $C_L = 100pF$ , 1V step	0.01%		8		μs
OUTPUT			'				
		D = 100k0 to 1/	Positive rail	(V+) – 1	(V+) - 0.75		
		$R_L$ = 100kΩ to V–	Negative rail		(V-) + 0.001	(V-) + 0.05	
\/ -	Voltago output	P 100kO	Positive rail	(V+) – 1	(V+) - 0.75		
Vo	Voltage output	$R_L = 100 k\Omega$	Negative rail		(V-) + 0.02	(V-) + 0.06	V
		P 10k0	Positive rail	(V+) – 1	(V+) - 0.75		
		$R_L = 10k\Omega$	Negative rail		(V-) + 0.2	(V-) + 0.3	
laa	Short-circuit current	Sourcing			7		mA
I <sub>SC</sub>	Onort-oroun current	Sinking			-10		IIIA
C <sub>L</sub>	Capacitive load drive			See Ty	pical Characte	ristics	
POWER S	SUPPLY						
IQ	Quiescent current per amplifier				150	350	μA

<sup>(1)</sup> Input bias current specified by design and processing.



## 5.6 Electrical Characteristics for $V_S = 5V$

at  $T_A$  = 25°C,  $V_O$  =  $V_S$  / 2, and  $R_L$  = 10k $\Omega$  connected to  $V_S$  / 2 (unless otherwise noted)

	PARAMETER	TEST COND	ITIONS	MIN	TYP	MAX	UNIT
OFFSET \	/OLTAGE						
V <sub>OS</sub>	Input offset voltage	V <sub>CM</sub> = 2.5V			±250	±750	μV
dV <sub>OS</sub> /dT	Input offset voltage drift	$T_A = -40$ °C to +85°C			±2	±5	μV/°C
PSRR	Power-supply rejection ratio	2.7V < V <sub>S</sub> < 36V			10	30	μV/V
	Channel separation (dual)				1		μV/V
INPUT BI	AS CURRENT			·			
I <sub>B</sub>	Input bias current (1)	V <sub>CM</sub> = 2.5V			-10	-40	nA
Ios	Input offset current (1)	V <sub>CM</sub> = 2.5V			±0.5	±10	nA
NOISE	•	•		-			
	Input voltage noise	f = 0.1Hz to 10Hz			1		μV <sub>PP</sub>
e <sub>n</sub>	Input voltage noise density	f = 1kHz			28		nV/√ <del>Hz</del>
in	Input current noise density	f = 1kHz			60		fA/√ <del>Hz</del>
INPUT VO	DLTAGE			-			
V <sub>CM</sub>	Common-mode voltage			(V-) - 0.2		(V+) - 1.5	V
CMRR	Common-mode rejection ratio	$V_{CM} = (V-) - 0.2V \text{ to } (V+) - 1.5V$		76	86		dB
INPUT IM	PEDANCE	ı					
_		Differential			5    4		MΩ    pF
Z <sub>IN</sub>	Input impedance	Common-mode			5    2		TΩ    pF
OPEN-LO	OP GAIN	ı					
A <sub>OL</sub>	Open-loop voltage gain	V <sub>O</sub> = 0.5V to 4V		75	88		dB
FREQUE	NCY RESPONSE	1					
GBW	Gain bandwidth product				1.4		MHz
SR	Slew rate	G = 1			0.45		V/µs
	Cattling time	C = 1 C = 100mF 3V ct	0.1%		11		
t <sub>S</sub>	Settling time	$G = -1$ , $C_L = 100pF$ , 3V step	0.01%		16		μs
ОИТРИТ	•	•					
		P. = 100kO to \/	Positive rail	(V+) - 1.5	(V+) - 0.75		
		$R_L = 100k\Omega$ to V–	Negative rail		(V-) + 0.001	(V-) + 0.1	
	Valtage cutput	D = 100k0	Positive rail	(V+) - 1.5	(V+) - 0.75		.,
Vo	Voltage output	$R_L = 100k\Omega$	Negative rail		(V-) + 0.04	(V-) + 0.12	
		D -40 k0	Positive rail	(V+) - 1.5	(V+) - 0.75		
		R <sub>L</sub> =10 kΩ	Negative rail		(V-) + 0.35	(V-) + 0.6	
	Ob and aims vite.	Sourcing	1		8		4
I <sub>SC</sub>	Short-circuit current	Sinking			-10		mA
CL	Capacitive load drive			See Ty	pical Characte	ristics	
POWER S	SUPPLY	ı		1			
IQ	Quiescent current per amplifier				170	350	μA

<sup>(1)</sup> Input bias current specified by design and processing.



# 5.7 Electrical Characteristics for $V_S = 30V$

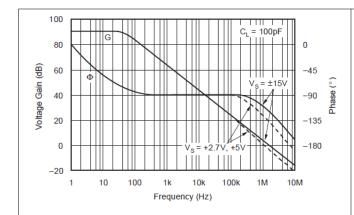
at  $T_A$  = 25°C,  $V_O$  =  $V_S$  / 2, and  $R_L$  = 10k $\Omega$  connected to  $V_S$  / 2 (unless otherwise noted)

	PARAMETER	TEST COND	TIONS	MIN	TYP	MAX	UNIT
OFFSET \	/OLTAGE						
V <sub>OS</sub>	Input offset voltage	$V_{CM} = V_S/2$			±350	±950	μV
dV <sub>OS</sub> /dT	Input offset voltage drift	$T_A = -40$ °C to +85°C			±2.5	±7	μV/°C
PSRR	Power-supply rejection ratio	2.7V < V <sub>S</sub> < 36V			10	30	μV/V
	Channel separation (dual)				1		μV/V
INPUT BIA	AS CURRENT						
I <sub>B</sub>	Input bias current (1)	$V_{CM} = V_S/2$			-8.5	-40	nA
I <sub>OS</sub>	Input offset current (1)	$V_{CM} = V_S/2$			±0.5	±10	nA
NOISE				<u> </u>			
	Input voltage noise	f = 0.1Hz to 10Hz			1		$\mu V_{PP}$
e <sub>n</sub>	Input voltage noise density	f = 1kHz			28		nV/√ <del>Hz</del>
i <sub>n</sub>	Input current noise density	f = 1kHz			80		fA/√ <del>Hz</del>
INPUT VO	DLTAGE			<u> </u>			
V <sub>CM</sub>	Common-mode voltage			(V-) - 0.2		(V+) - 1.5	V
CMRR	Common-mode rejection ratio	V <sub>CM</sub> = (V–) to (V+) – 1.5V		80	90		dB
INPUT IM	PEDANCE			<u>'</u>			
-		Differential			5    4		MΩ    pF
Z <sub>IN</sub>	Input impedance	Common-mode			5    2		TΩ    pF
OPEN-LO	OP GAIN			•			
A <sub>OL</sub>	Open-loop voltage gain	V <sub>O</sub> = (V–) + 1V to (V+) – 1.2V		80	88		dB
FREQUE	NCY RESPONSE						
GBW	Gain bandwidth product				1.5		MHz
SR	Slew rate	G = 1			0.44		V/µs
	0-111:	0 - 4 0 - 400-5 401/	0.1%		20		
ts	Settling time	G = -1, C <sub>L</sub> = 100pF, 10V step	0.01%		24		μs
OUTPUT			'	•			
		D = 400k0	Positive rail	(V+) - 1.2	(V+) - 0.9		
V	\/-lk	$R_L = 100k\Omega$	Negative rail		(V-) + 0.3	(V-) + 0.5	1
Vo	Voltage output	D 401.0	Positive rail	(V+) - 1.2	(V+) - 0.9		V
		$R_L = 10k\Omega$	Negative rail		(V-) + 0.85	(V-) + 1	
	01 1 : :1	Sourcing			9.5		
I <sub>SC</sub>	Short-circuit current	Sinking			-10		mA
C <sub>L</sub>	Capacitive load drive			See Typical Characteristics			
POWER S	SUPPLY			<u>'</u>			
IQ	Quiescent current per amplifier				200	475	μА

<sup>(1)</sup> Input bias current specified by design and processing.



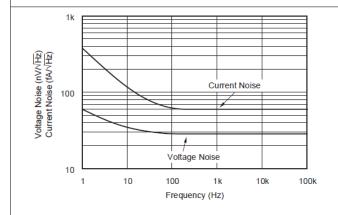
### **5.8 Typical Characteristics**



+PSR (V<sub>S</sub> = +5V, ±15V) 100 80 CMR (dB) 60 +PSR PSR, = +2.7 40 20 PSR  $= \pm 15V$ 0 10 100 10k 100k 1M 10M Frequency (Hz)

Figure 5-1. Open-Loop Gain and Phase vs Frequency

Figure 5-2. Power Supply and Common-Mode Rejection vs Frequency



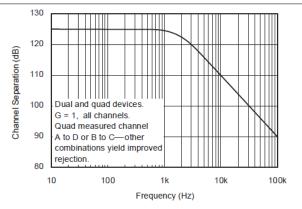
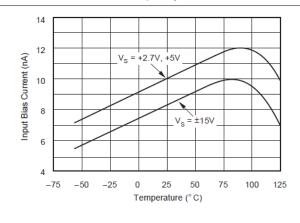


Figure 5-3. Input Noise and Current Noise Spectral Density vs Frequency

Figure 5-4. Channel Separation vs Frequency



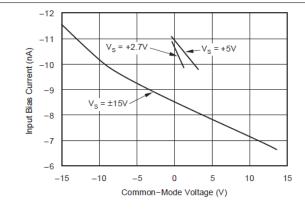


Figure 5-5. Input Bias Current vs Temperature

Figure 5-6. Input Bias Current vs Input Common-Mode Voltage

## **5.8 Typical Characteristics (continued)**

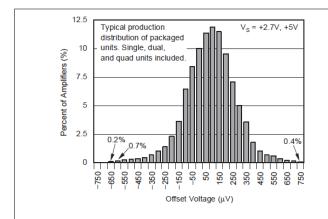
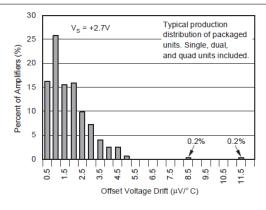


Figure 5-7. Offset Voltage Production Distribution





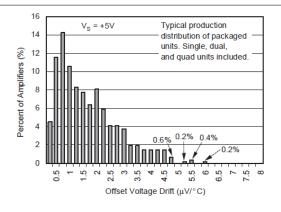
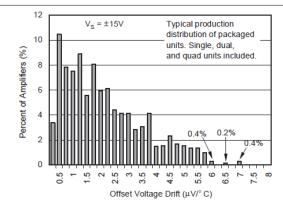


Figure 5-9. Offset Voltage Drift Production Distribution

Figure 5-10. Offset Voltage Drift Production Distribution



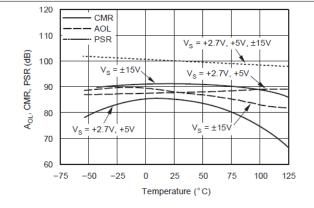
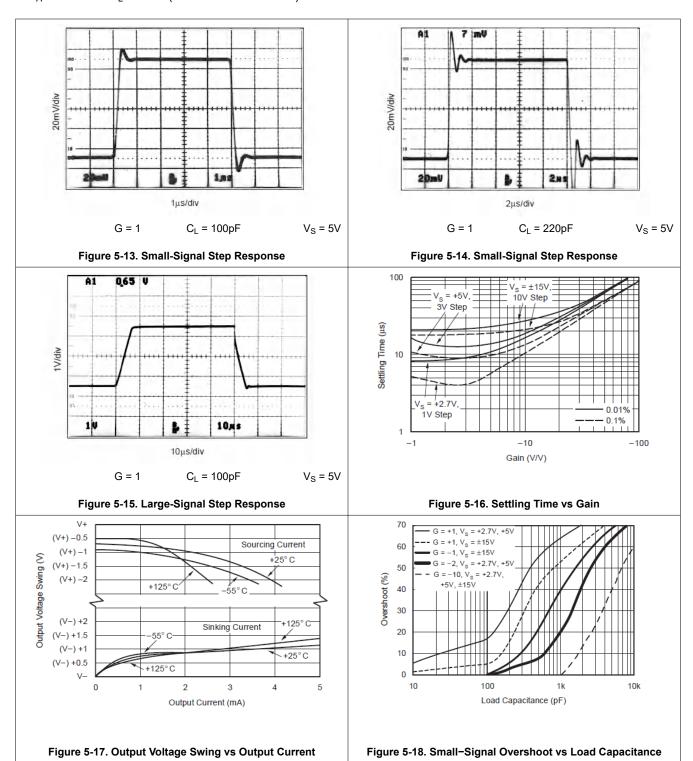


Figure 5-11. Offset Voltage Drift Production Distribution

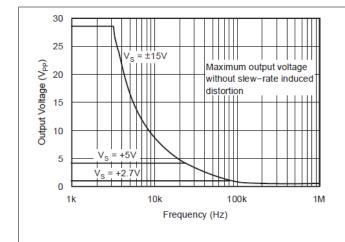
Figure 5-12.  $A_{OL}$ , CMR, PSR vs Temperature



## 5.8 Typical Characteristics (continued)



## **5.8 Typical Characteristics (continued)**



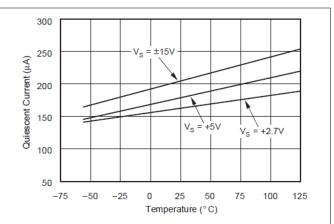


Figure 5-19. Maximum Output Voltage vs Frequency



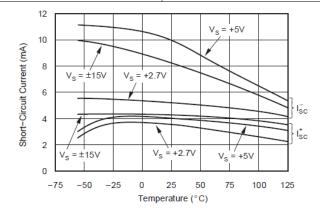


Figure 5-21. Short-Circuit Current vs Temperature

## 6 Application and Implementation

#### Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

#### **6.1 Application Information**

The OPA237 series op amps are unity-gain stable and an excellent choice for a wide range of general-purpose applications. Bypass the power-supply pins with 10nF ceramic capacitors.

#### 6.1.1 Operating Voltage

OPA237 series op amps operate from single (2.7V to 36V) or dual (±1.35V to ±18V) supplies with excellent performance. Most behavior remains unchanged throughout the full operating voltage range. Parameters that vary significantly with operating voltage are shown in *Typical Characteristics*. Specifications are production tested with 2.7V, 5V, and ±15V supplies.

#### 6.1.2 Output Current and Stability

OPA237 series op amps can drive large capacitive loads. However, under certain limited output conditions, any op amp can become unstable. Figure 6-2 shows the region where the OPA237 has a potential for instability. These load conditions are rarely encountered, especially for single-supply applications. For example, when a 5V supply with a  $10k\Omega$  load to  $V_S/2$  is used.

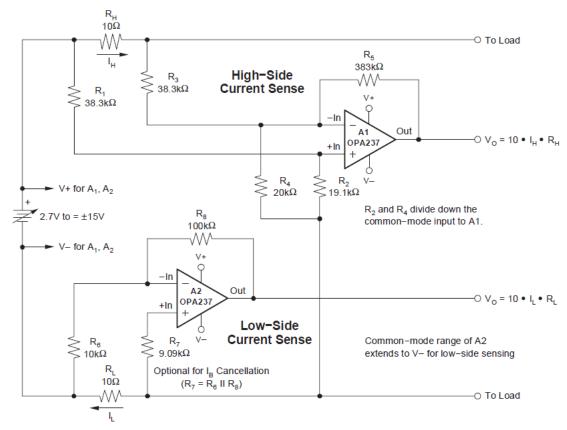
OPA237 series op amps remain stable with capacitive loads up to 4,000pF, if sinking current, and up to 10,000pF, if sourcing current. Furthermore, in single-supply applications where the load is connected to ground, the op amp is only sourcing current, and as Figure 6-2 shows, the op amp can drive 10,000pF with output currents up to 1.5mA.

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### 6.2 Typical Application



Note: Low-side and high-side sensing circuits can be used independently.

Figure 6-1. Low-Side and High-Side Battery Current Sensing

#### 6.2.1 Application Curve

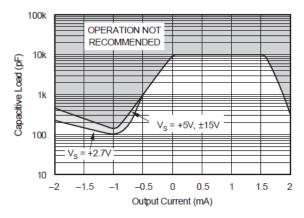


Figure 6-2. Stability-Capacitive Load vs Output Current



## 7 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

#### 7.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

#### 7.2 Support Resources

TI E2E™ support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

#### 7.3 Trademarks

TI E2E<sup>™</sup> is a trademark of Texas Instruments.

All trademarks are the property of their respective owners.

### 7.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

## 7.5 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

## **8 Revision History**

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

CI	hanges from Revision A (February 2007) to Revision B (April 2025)	Page
•	Updated the numbering format for tables, figures, and cross-references throughout the document	1
•	Changed quiescent current unit from µV to µA in Features	1
•	Updated Pin Configurations and Functions to latest standards and added Pin Functions tables	3
•	Added input current to Absolute Maximum Ratings	4
•	Added Recommended Operating Conditions	4
•	Added Thermal Information	
•	Updated junction-to-ambient thermal resistance for OPA237 packages	4
•	Updated junction-to-ambient thermal resistance for OPA2237 packages	4
•	Updated all Electrical Characteristics tables to latest format	5
•	Added test condition V <sub>O</sub> = V <sub>S</sub> /2	<mark>5</mark>
•	Changed maximum input offset voltage from ±750µV to ±950µV	
•	Deleted table note "Specified by wafer-level test to 95% confidence"	
•	Changed maximum input offset voltage drift from 5μV/°C to 7.5μV/°C	
•	Updated table note 1	
•	Updated V <sub>CM</sub> range format to refer to rails	
•	Changed minimum common-mode rejection ratio from 75dB to 71dB	5
•	Changed differential input impedance from 5·10 <sup>6</sup> Ω to 5MΩ	5
•	Changed common-mode input impedance from $5\cdot10^9\Omega$ to $5T\Omega$	
•	Changed minimum open-loop voltage gain from 80dB to 75dB	<mark>5</mark>

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•	Changed test condition for open-loop voltage gain from 0.5V to 0.55V	
_		
•	Added V- to negative rail rows and moved positive and negative labels to test condtions for voltage output	
•	Changed test condition of voltage output for $R_L$ = 100k $\Omega$ from "Ground" to V	.5
•	Changed maximum voltage output for $R_L = 100 k\Omega$ from negative rail from 0.01V to (V–) + 0.05V	. 5
•	Updated short circuit current to show separated rows for source and sink	
•	Changed short-circuit sourcing current from 3.5mA to 7mA	5
•	Changed short-circuit sinking current from -5mA to -10mA	.5
•	Changed typical quiescent current from 160µA to 150µA	.5
•	Added test condition $V_O = V_S/2$	. 6
•	Deleted table note "Specified by wafer-level test to 95% confidence"	. 6
•	Changed channel separation from 0.5μV/V to 1μV/V	
•	Updated table note 1	. 6
•	Updated V <sub>CM</sub> range format to refer to rails	.6
•	Changed minimum common-mode rejection ratio for from 78dB to 76dB	6
•	Changed differential input impedance from $5\cdot10^6\Omega$ to $5M\Omega$	
•	Changed common-mode input impedance from $5\cdot10^9\Omega$ to $5T\Omega$	
•	Changed typical slew rate from 0.5V/µs to 0.45V/µs	
•	Added V- to negative rail rows and moved positive and negative labels to test conditions for voltage output.	
•	Changed test condition of voltage output for RL = $100k\Omega$ from "Ground" to V	
•	Changed minimum voltage output from positive rail from (V+) – 1V to (V+) – 1.5V	
•	Changed maximum voltage output from negative rail from $(V-) + 0.01V$ to $(V-) + 0.1V$	
•	Changed minimum voltage output from positive rail from $(V+) - 1V$ to $(V+) - 1.5V$	
•	Changed maximum voltage output from negative rail from (V–) + 0.5V to (V–) + 0.6V	
•	Updated short circuit current to show separated rows for source and sink	
•	Changed short-circuit sourcing current from 4mA to 8mA	
•	Added test condition $V_O = V_S/2$	
•	Changed test condition for input offset voltage from $V_{CM} = 0V$ to $V_{CM} = V_S/2$	
•	Deleted table note "Specified by wafer-level test to 95% confidence"	
•	Changed channel separation from 0.5µV/V to 1µV/VUpdated table note 1	
•	Changed test condition for input bias current from $V_{CM} = 0V$ to $V_{CM} = V_S/2$	
	Changed test condition for input bias current from $V_{CM} = 0V$ to $V_{CM} = V_S/2$	
	Changed input current noise density from $60fA/\sqrt{Hz}$ to $80fA/\sqrt{Hz}$	
•	Updated V <sub>CM</sub> range format to refer to rails	
	Changed differential input impedance from $5\cdot10^6\Omega$ to $5M\Omega$	7
	Changed common-mode input impedance from $5 \cdot 10^9 \Omega$ to $5 T \Omega$ .	
	Changed slew rate from 0.5V/µs to 0.44V/µs	
	Changed settling time in 0.1% from 18µs to 20µs	7
	Changed settling time in 0.01% from 21µs to 24µs	
	Added V– to negative rail rows and moved positive and negative labels to test condtions for voltage output	
	Updated short circuit current to show separated rows for source and sink	
•	Changed short-circuit sourcing current from 4.5mA to 9.5mA	
•	Changed short-circuit sinking current from –8mA to –10mA	
•	Deleted ± sign from quiescent current spec	

## 9 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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## **PACKAGING INFORMATION**

Orderable part number	Status	Material type	Package   Pins	Package qty   Carrier	<b>RoHS</b> (3)	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
OPA2237EA/250	Last Time Buy	Production	VSSOP (DGK)   8	250   SMALL T&R	Yes	NIPDAUAG	Level-2-260C-1 YEAR	-	B37A
OPA2237EA/2K5	Active	Production	VSSOP (DGK)   8	2500   LARGE T&R	Yes	Call TI   Nipdauag   Nipdau	Level-2-260C-1 YEAR	-40 to 85	B37A
OPA2237EA/2K5.A	Active	Production	VSSOP (DGK)   8	2500   LARGE T&R	Yes	Call TI	Level-2-260C-1 YEAR	-40 to 85	B37A
OPA2237EA/2K5.B	Active	Production	VSSOP (DGK)   8	2500   LARGE T&R	Yes	Call TI	Level-2-260C-1 YEAR	-40 to 85	B37A
OPA2237UA	Last Time Buy	Production	SOIC (D)   8	75   TUBE	Yes	NIPDAU	Level-3-260C-168 HR	-	OPA 2237UA
OPA2237UA/2K5	Active	Production	SOIC (D)   8	2500   LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-	(OP2237, OPA) 2237UA
OPA2237UA/2K5.A	Active	Production	SOIC (D)   8	2500   LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 85	(OP2237, OPA) 2237UA
OPA2237UA/2K5.B	Active	Production	SOIC (D)   8	2500   LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 85	(OP2237, OPA) 2237UA
OPA2237UAE4	Active	Production	SOIC (D)   8	75   TUBE	-	Call TI	Call TI	See OPA2237UA	
OPA237NA/250	Last Time Buy	Production	SOT-23 (DBV)   5	250   SMALL T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 70	A37A
OPA237NA/3K	Active	Production	SOT-23 (DBV)   5	3000   LARGE T&R	Yes	NIPDAU   SN	Level-2-260C-1 YEAR	-40 to 70	A37A
OPA237NA/3K.A	Active	Production	SOT-23 (DBV)   5	3000   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 70	A37A
OPA237NA/3K.B	Active	Production	SOT-23 (DBV)   5	3000   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 70	A37A
OPA237NA/3K1G4	Active	Production	SOT-23 (DBV)   5	3000   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 70	A37A
OPA237NA/3K1G4.A	Active	Production	SOT-23 (DBV)   5	3000   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 70	A37A
OPA237UA	Last Time Buy	Production	SOIC (D)   8	75   TUBE	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 70	OPA 237UA
OPA237UA/2K5	Active	Production	SOIC (D)   8	2500   LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 70	(OP237, OPA) 237UA
OPA237UA/2K5.A	Active	Production	SOIC (D)   8	2500   LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 70	(OP237, OPA) 237UA
OPA237UA/2K5.B	Active	Production	SOIC (D)   8	2500   LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 70	(OP237, OPA) 237UA

<sup>(1)</sup> Status: For more details on status, see our product life cycle.



## PACKAGE OPTION ADDENDUM

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- (2) Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.
- (3) RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.
- (4) Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.
- (5) MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.
- (6) Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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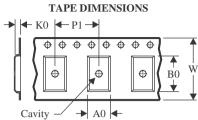
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# **PACKAGE MATERIALS INFORMATION**

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### TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
OPA2237EA/250	VSSOP	DGK	8	250	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
OPA2237EA/2K5	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
OPA2237UA/2K5	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
OPA237NA/250	SOT-23	DBV	5	250	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
OPA237NA/3K	SOT-23	DBV	5	3000	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
OPA237NA/3K1G4	SOT-23	DBV	5	3000	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
OPA237UA/2K5	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1



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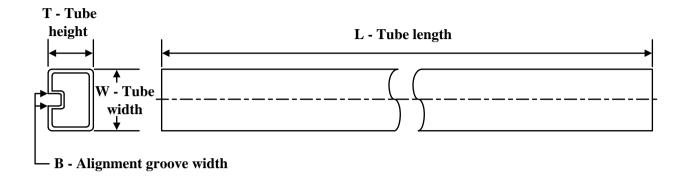
## \*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
OPA2237EA/250	VSSOP	DGK	8	250	366.0	364.0	50.0
OPA2237EA/2K5	VSSOP	DGK	8	2500	366.0	364.0	50.0
OPA2237UA/2K5	SOIC	D	8	2500	353.0	353.0	32.0
OPA237NA/250	SOT-23	DBV	5	250	180.0	180.0	18.0
OPA237NA/3K	SOT-23	DBV	5	3000	180.0	180.0	18.0
OPA237NA/3K1G4	SOT-23	DBV	5	3000	180.0	180.0	18.0
OPA237UA/2K5	SOIC	D	8	2500	353.0	353.0	32.0

# **PACKAGE MATERIALS INFORMATION**

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### **TUBE**



#### \*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
OPA2237UA	D	SOIC	8	75	506.6	8	3940	4.32
OPA237UA	D	SOIC	8	75	506.6	8	3940	4.32



SMALL OUTLINE TRANSISTOR



#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
  2. This drawing is subject to change without notice.
  3. Reference JEDEC MO-178.

- 4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.
- 5. Support pin may differ or may not be present.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.





SMALL OUTLINE PACKAGE



#### NOTES:

PowerPAD is a trademark of Texas Instruments.

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-187.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
- 8. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.
- 9. Size of metal pad may vary due to creepage requirement.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 11. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 12. Board assembly site may have different recommendations for stencil design.





SMALL OUTLINE INTEGRATED CIRCUIT



### NOTES:

- 1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
- 4. This dimension does not include interlead flash.
- 5. Reference JEDEC registration MS-012, variation AA.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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